

DATA SHEET

SCHOTTKY BARRIER RECTIFIERS

VOLTAGE 100 Volts

CURRENT 20.0Amperes

ITO-220AB

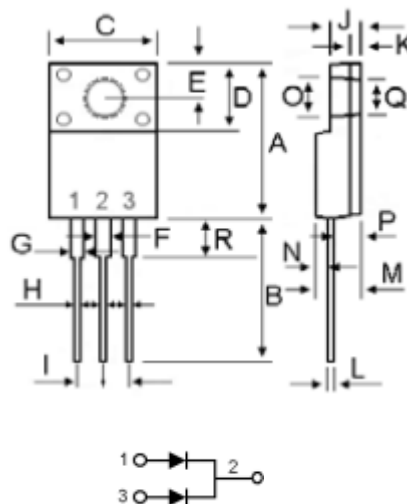
Unit:mm

FEATURES

- Metal of silicon rectifier,majority carrier conducton
- Guard-Ring for Stress Protection.
- Low power loss, high efficiency
- High current capability, low VF
- High surge capacity
- Plastic package has UL flammability classification 94V-0

MECHANICAL DATA

- Case : ITO-220AB molded plastic
- Polarity : As marked on the body
- Mounting position : Any



DIM	MILLIMETERS	
	MIN	MAX
A	15.67	16.07
B	12.90	13.30
C	9.96	10.36
D	6.50	6.90
E	2.65	2.75
F	1.20	1.24
G	1.26	1.46
H	0.70	0.90
I	2.34	2.74
J	2.32	2.72
K	0.60	0.90
L	0.45	0.60
M	4.53	4.93
N	1.30	1.70
O	3.35	3.45
P	2.56	2.96
Q	3.15	3.25
R	2.20	2.45



In compliance with EU RoHs 2002/95/EC directives

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60HZ, resistive or inductive load.

For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL			MBR20100FCT	UNIT
Maximum Recurrent Peak Reverse Voltage	VRRM			100	V
Maximum RMS Voltage	VRMS			70	V
Maximum DC Blocking Voltage	Vcc			100	V
Average Rectifier Forward Current (per diode)	IF(AV)			10	A
Total Device (Rated VR) @TC=125°C				20	
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware, single phase, 60Hz)	IFSM			150	A
Maximum Instantaneous Forward Voltage	IF=10A	Tc=25°C	VF	0.85	V
		Tc=125°C		0.75	
Instantaneous Reverse Current	AT VRM	Tc=25°C	IR	0.05	MA
		Tc=125°C		15	
Typical Thermal Resistance	R0JC			3.5	°C/W
Operating Temperature Range	TJ			-55to+175	°C
Storage Temperature Range	TSTG			-55to+175	°C

FIG-1 FORWARD CURRENT DERATING CURVE

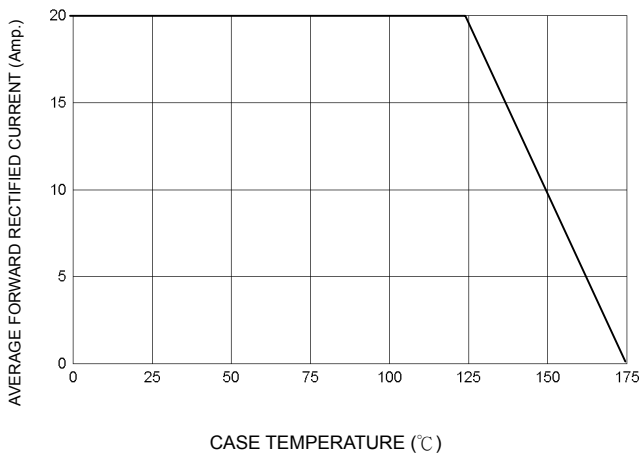


FIG-2 TYPICAL FORWARD CHARACTERISTICS

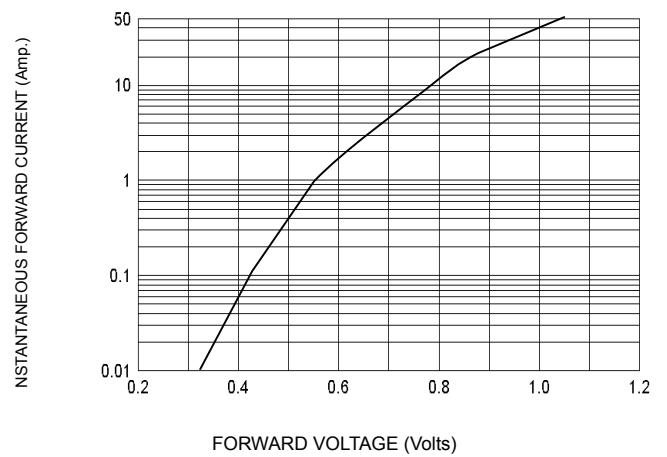


FIG-3 TYPICAL REVERSE CHARACTERISTICS

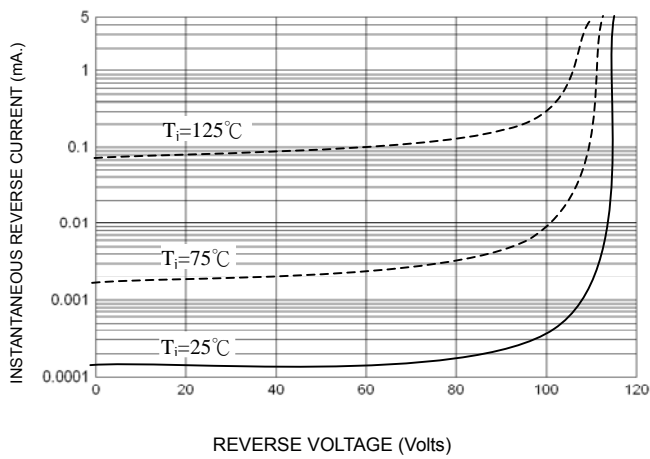


FIG-4 TYPICAL JUNCTION CAPACITANCE

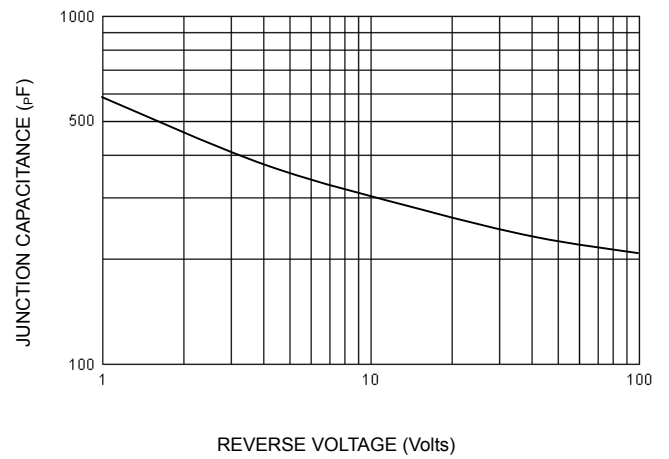


FIG-5 PEAK FORWARD SURGE CURRENT

